

High-Speed Opto-Electronic Components for Digital and Analog RF Systems

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WOCC

April 23, 2005

Multiplex, Inc.

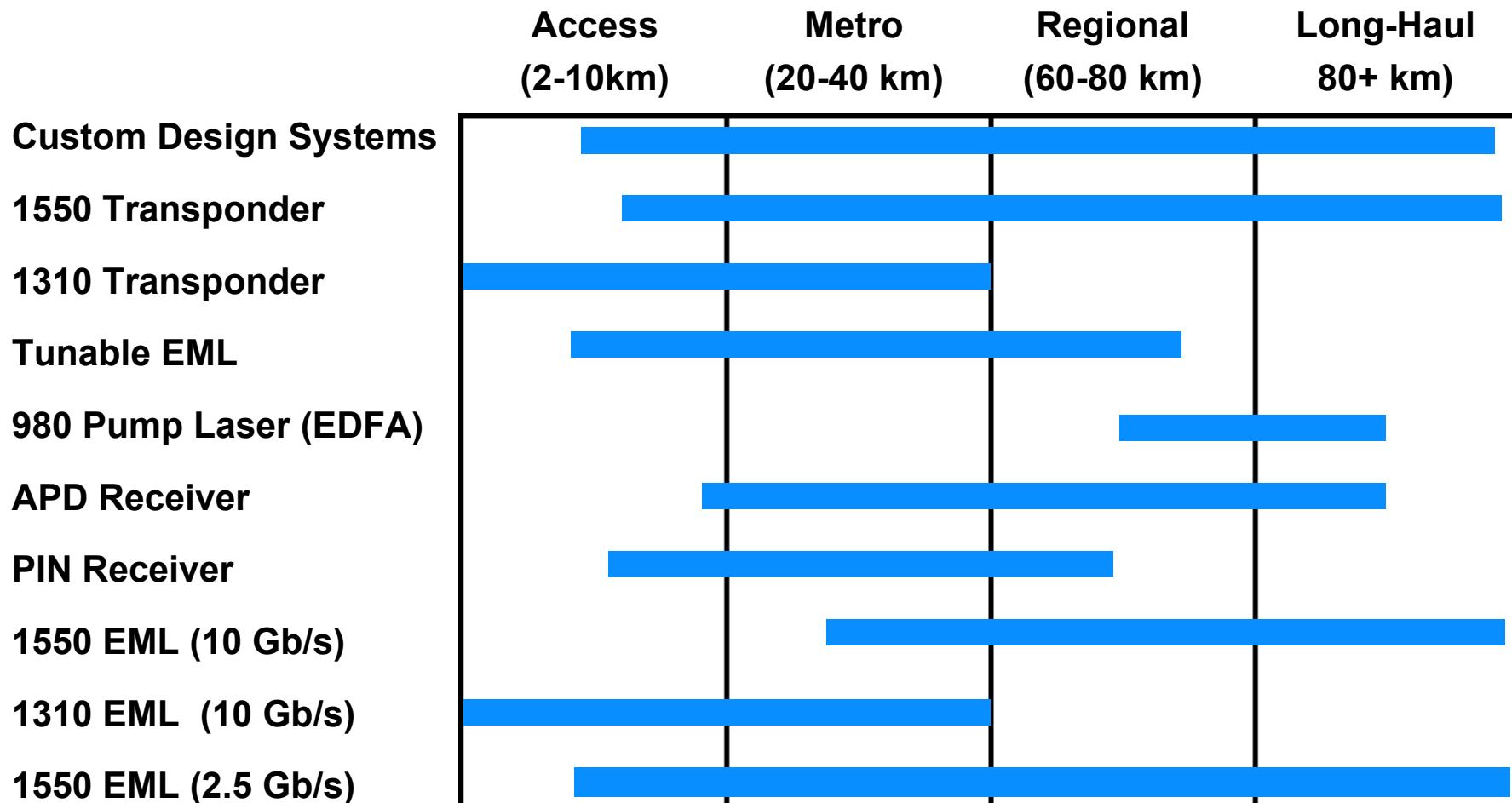
Photonics for Communications



5000 Hadley Road
South Plainfield, NJ 07080 USA

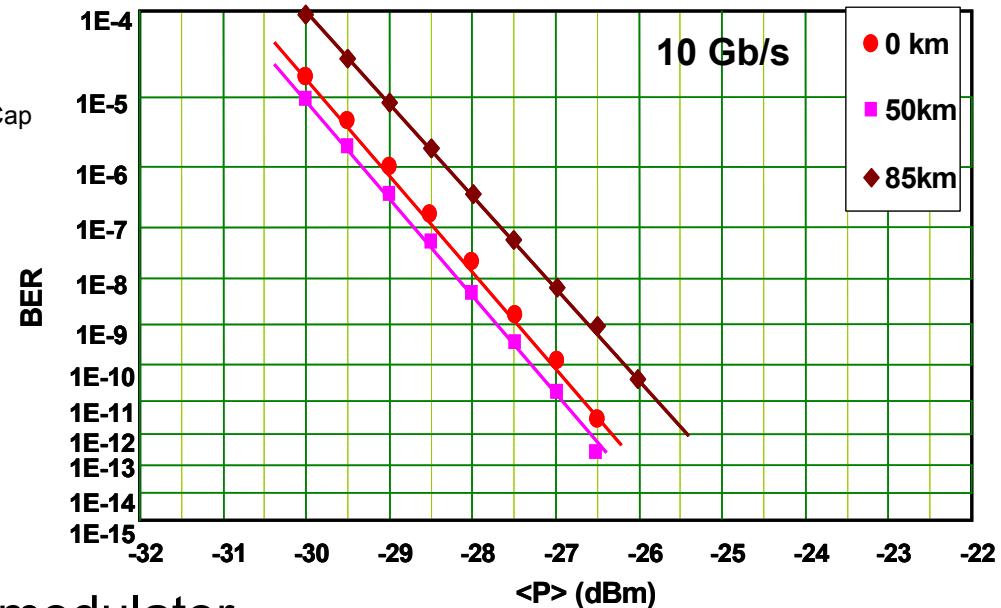
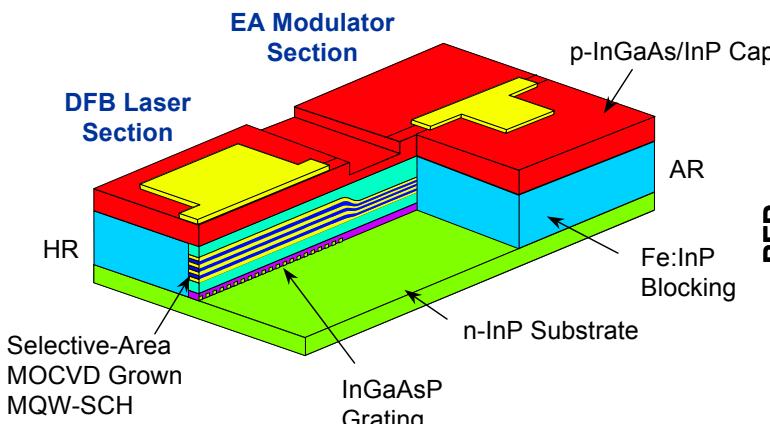
www.multiplexinc.com

Active Opto-Electronic Component Solutions for Optical Networks



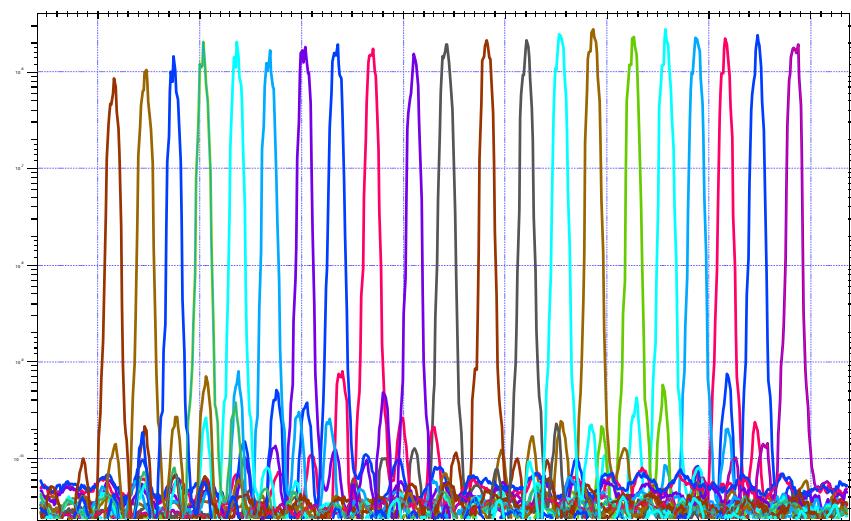
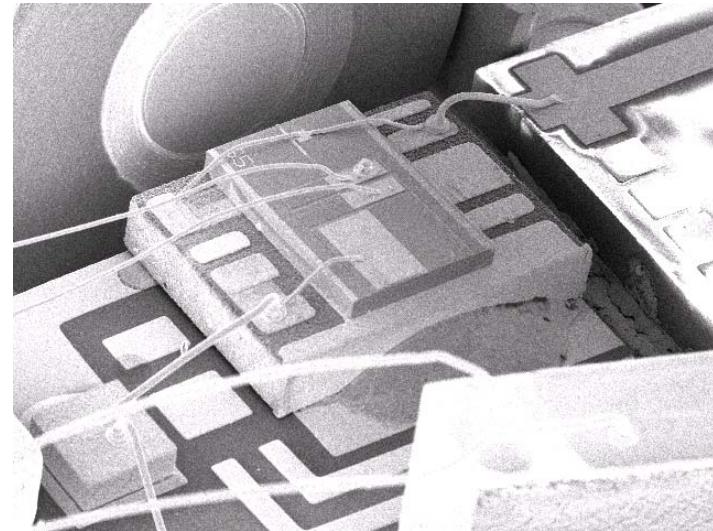
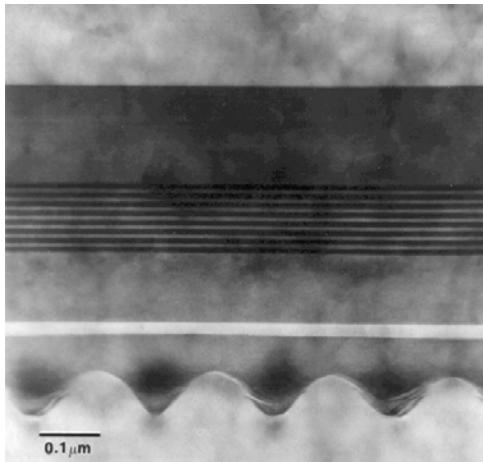
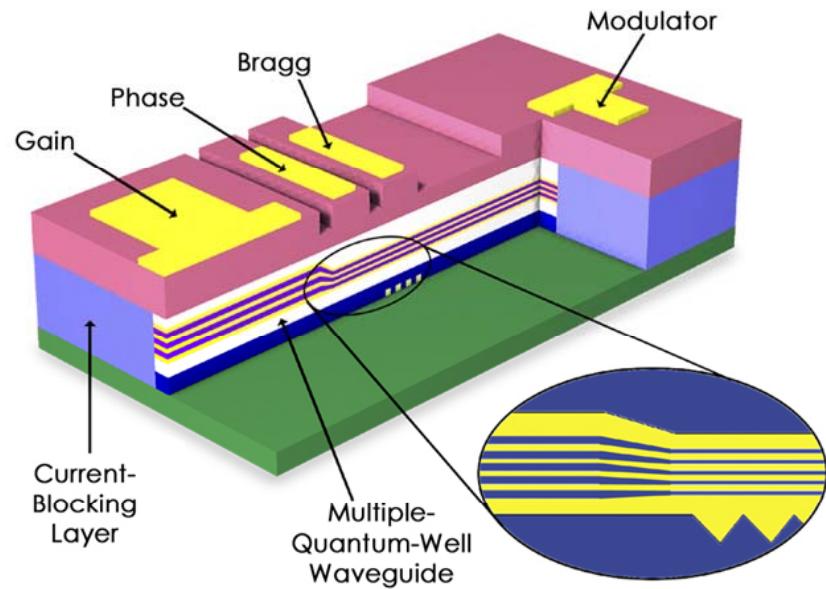
* 2.5Gb/s application extends to >640 km

Electro-absorption Modulated Laser (EML)



- MQW DFB laser and EA modulator
- Low cost integration by SAG (selective area growth)
- Fiber packaging same as DFB laser
- 80-km DWDM transmission
- Replaces hybrid-packaged Laser-LiNbO₃ modulators even for long-haul DWDM

Wavelength Tunable EML



1542

Wavelength (nm.)

1556

From MOCVD Wafer Growth to Subsystems and Fiber Transmission Test



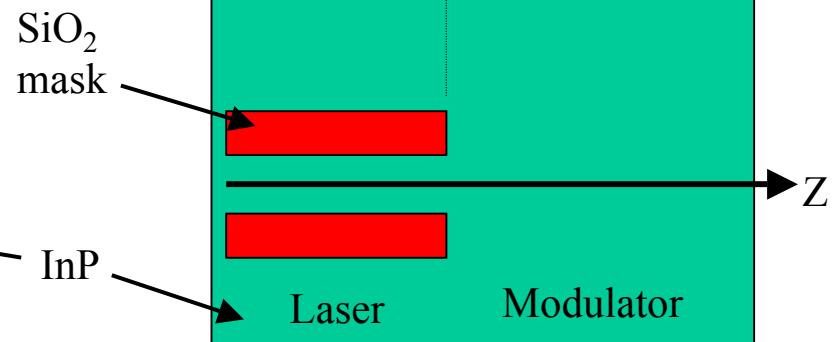
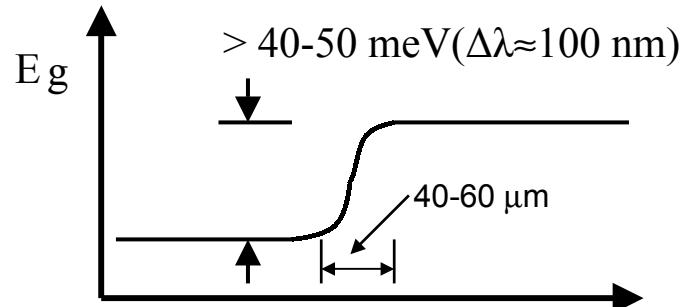
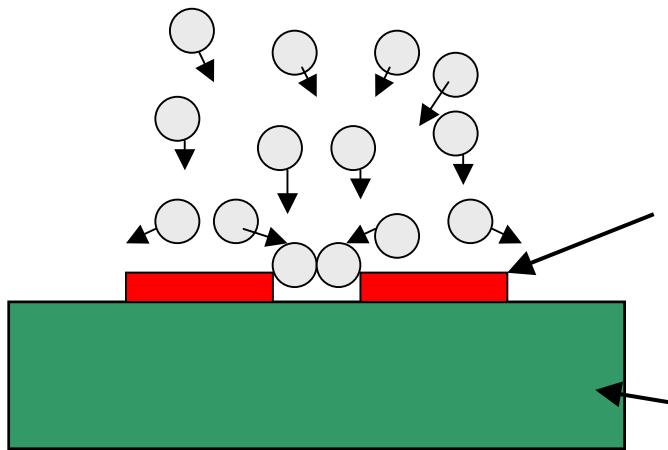
Selective Area MOVPE Growth

Increased concentration

Group III Precursors

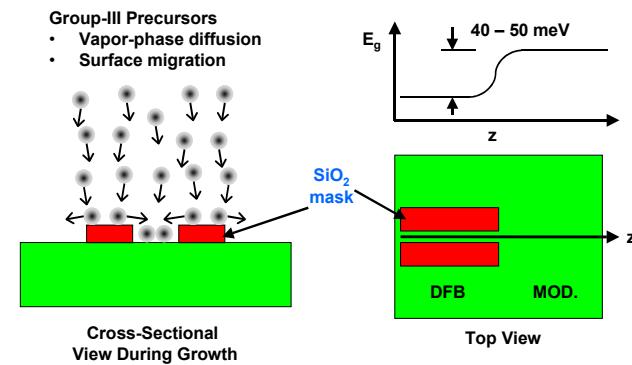
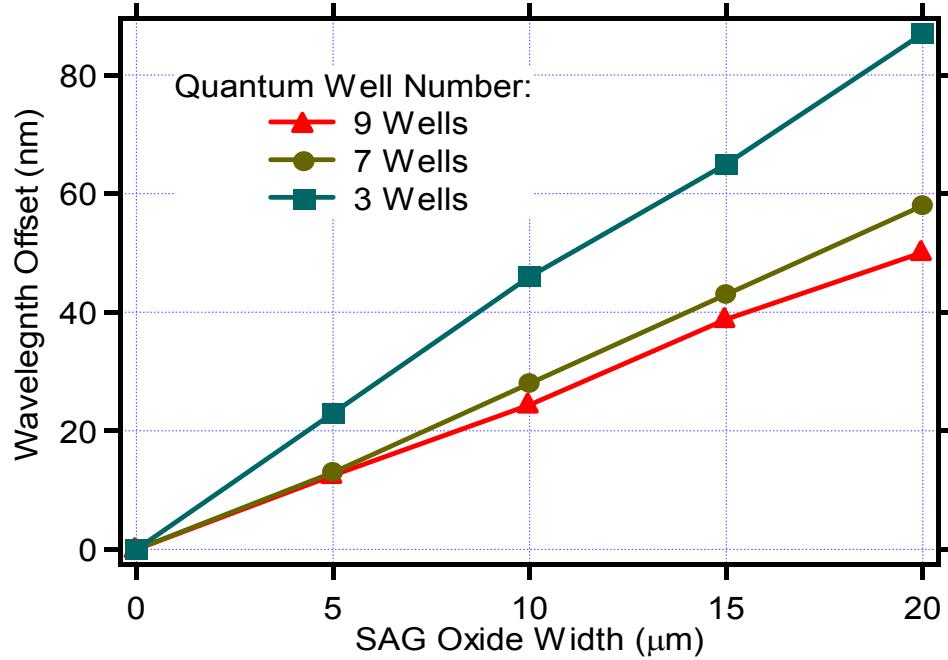
Enhanced

- Vapor phase diffusion
- Surface migration



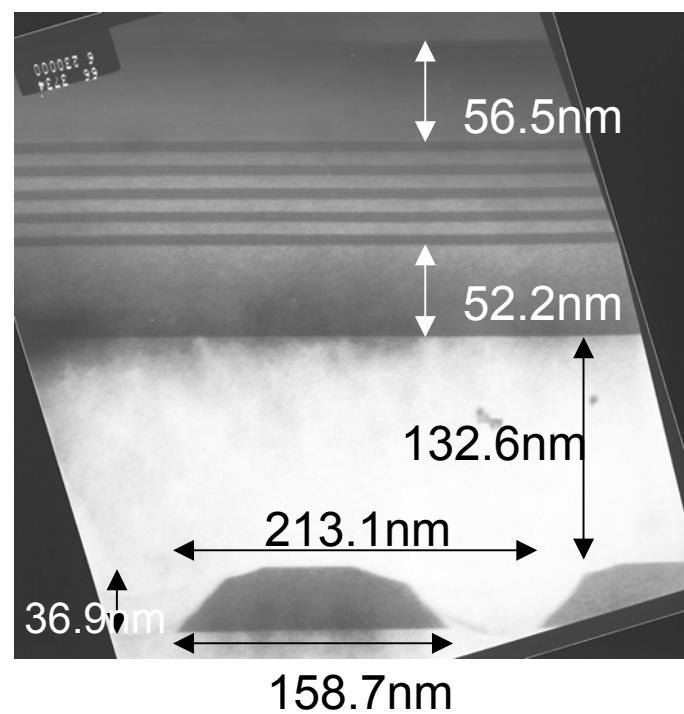
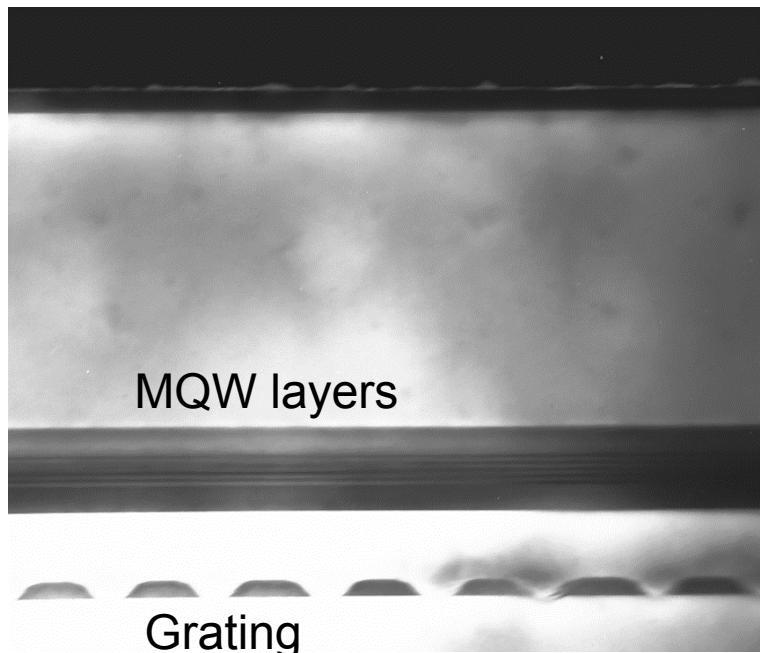
- (1) Indium rich (compressive strain) MQW inside slot
- (2) Thicker MQW layers inside the slot (Red shifted)

Micro Photo Luminescent Measurement

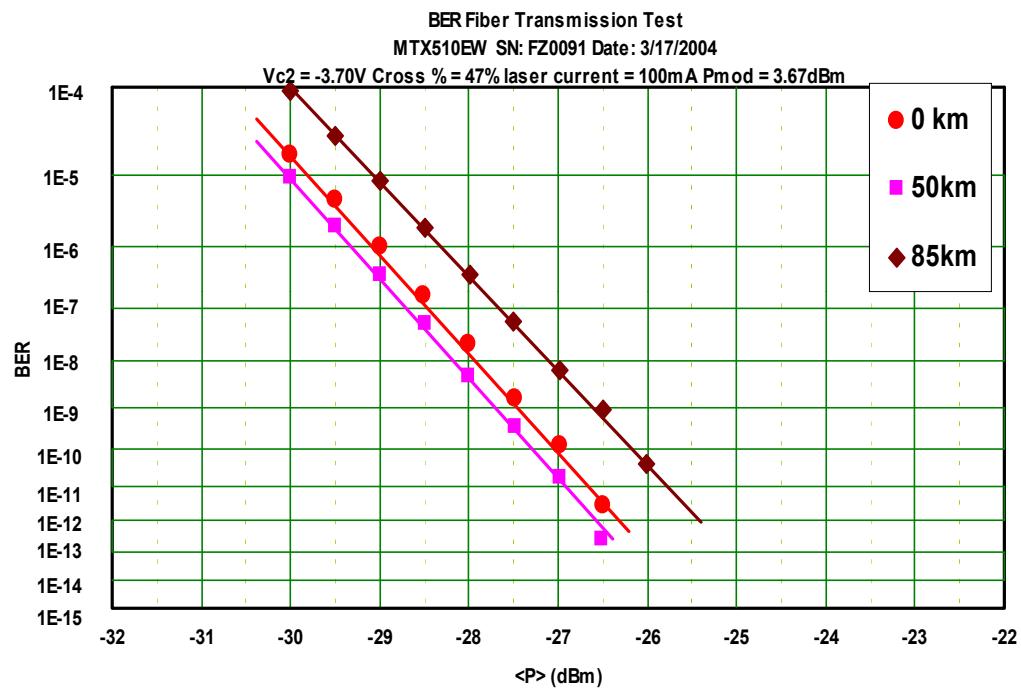


- Calibration of SAG-MOCVD growth
- Bandgap λ shift by well thickness (and alloy composition, strain)
- SAG mask design for active (source, modulator, detector) and passive waveguide integration

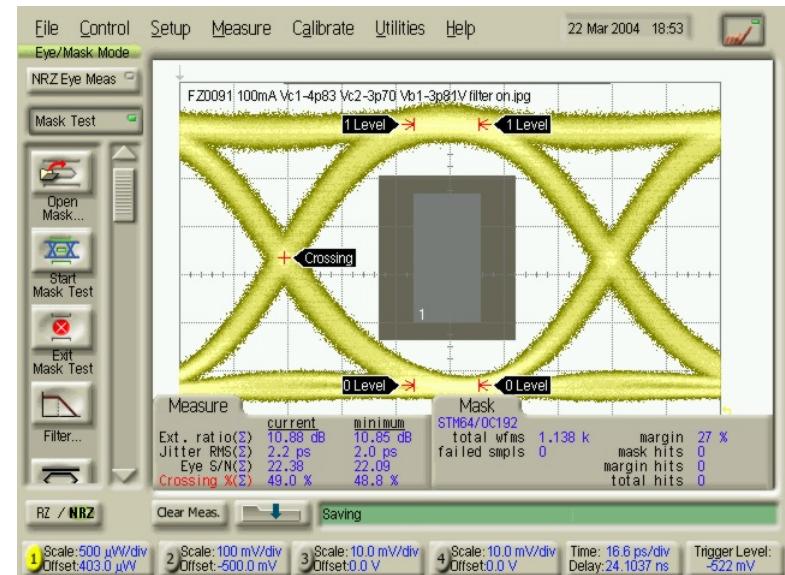
Cross-sectional Transmission Electron Microscopy of MQW and DFB Grating Structure



10 Gb/s 85km EML Module

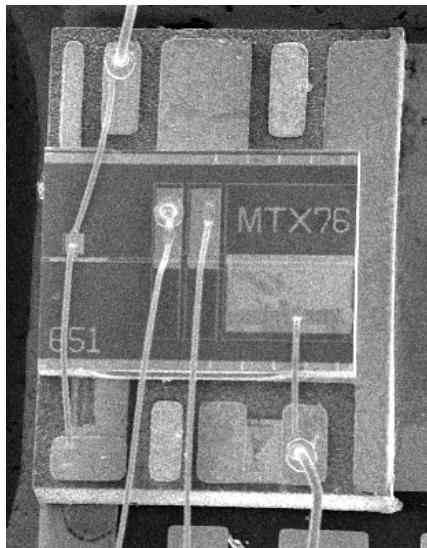
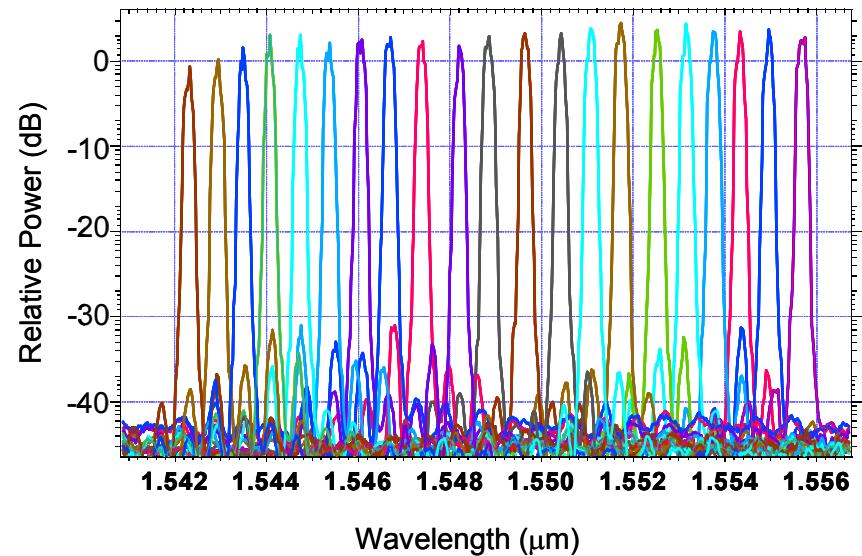
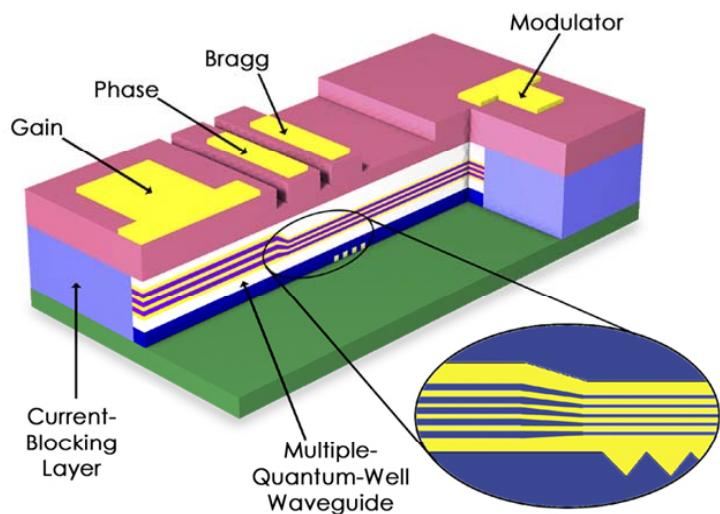


Laser operating current 100mA,
modulated power 3.67dBm

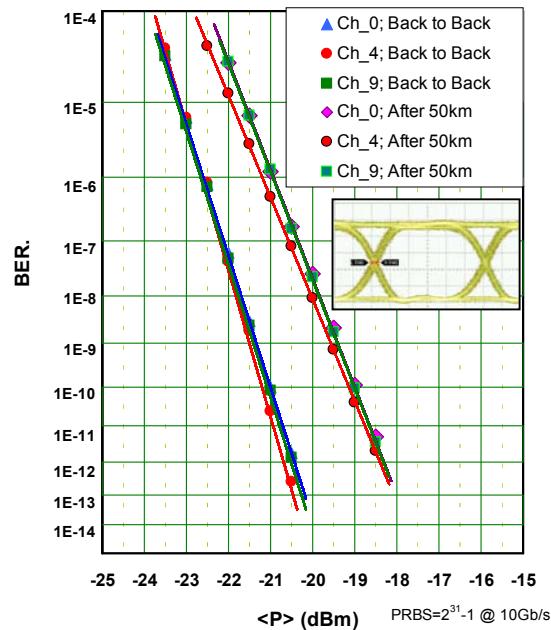


Filtered eye diagram of 85km EML module

Tunable EML (DBR laser+EA modulator)

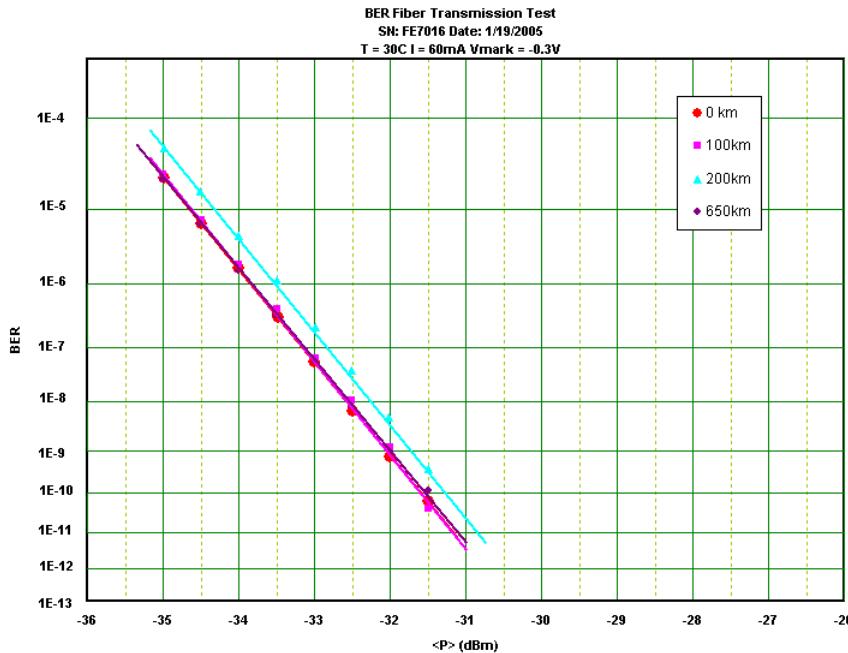


10 Gb/s TEML



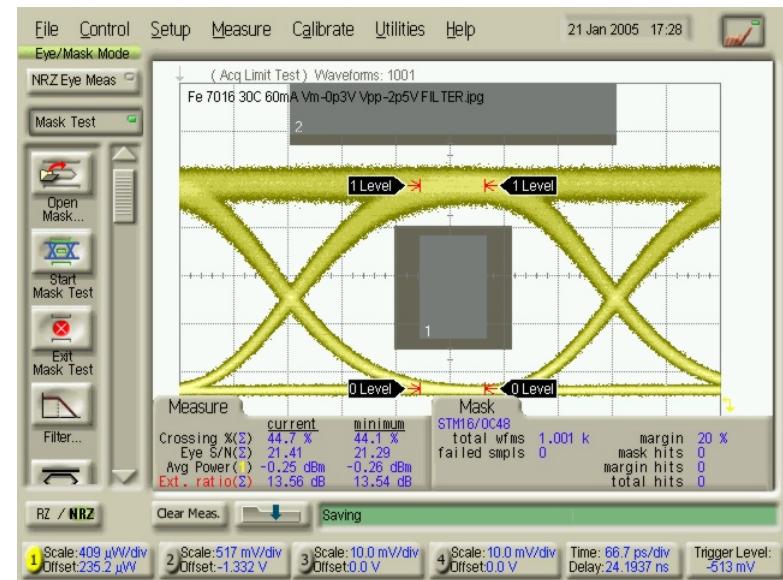
- Wavelength tuning characteristics (12 nm range)
- Fiber transmission test at 50-GHz spaced ITU channels

2.5 Gb/s 640km EML Module



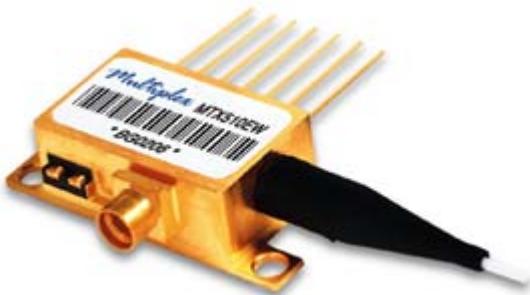
Laser operating current 60mA,
modulated power 0.07dBm

Integrated wavelength locker
for DWDM



Filtered eye diagram of 640km 2.5 Gb/s EML module

The Multiplex Family of EMLs



Gen-1 EML

7-pin with GPO

Industry-standard configuration

Qualified to Telcordia GR-468-CORE



Gen-2 EML

14-pin butterfly package

30GHz through pin replaces GPO

EML driver IC inside package

Qualified to Telcordia GR-468-CORE



Gen-3 EML

21-pin package

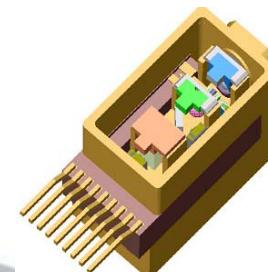
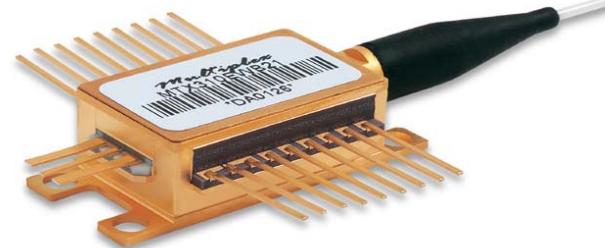
50GHz RF feed-through pins

G-S-G coplanar 50 Ohms ports

Integrated driver IC and wavelength locker

Next Generation EML Products

- 2.5G EML w/WLL - Current Product
- 10G GPO EML w/WLL - March/2005
- 10G Tunable EML w/WLL
(5nm Tuning Range) - Current Product
- 10G Tunable EML w/WLL
(12nm Tuning Range) - Q3/2005
- Miniature 10G Tunable EML w/WLL - Q3/2005



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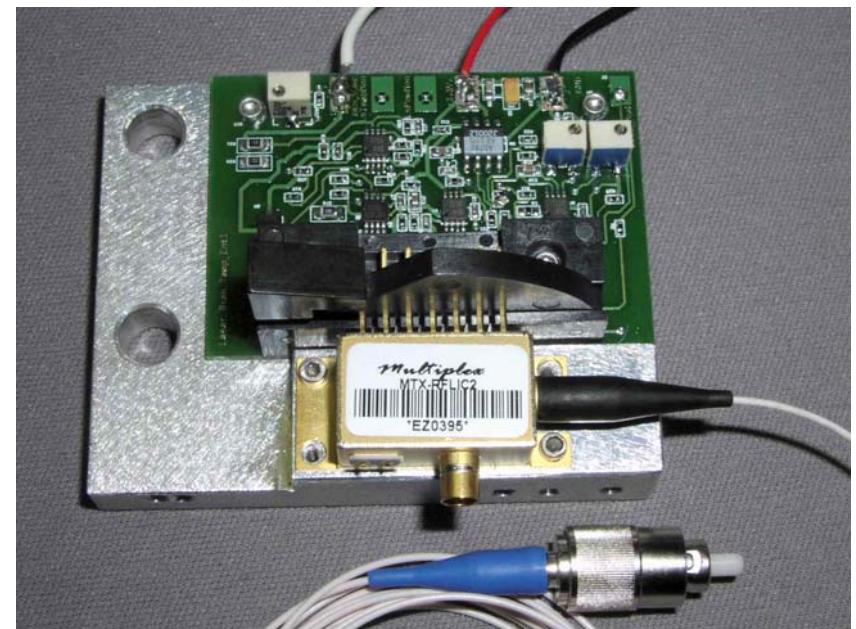
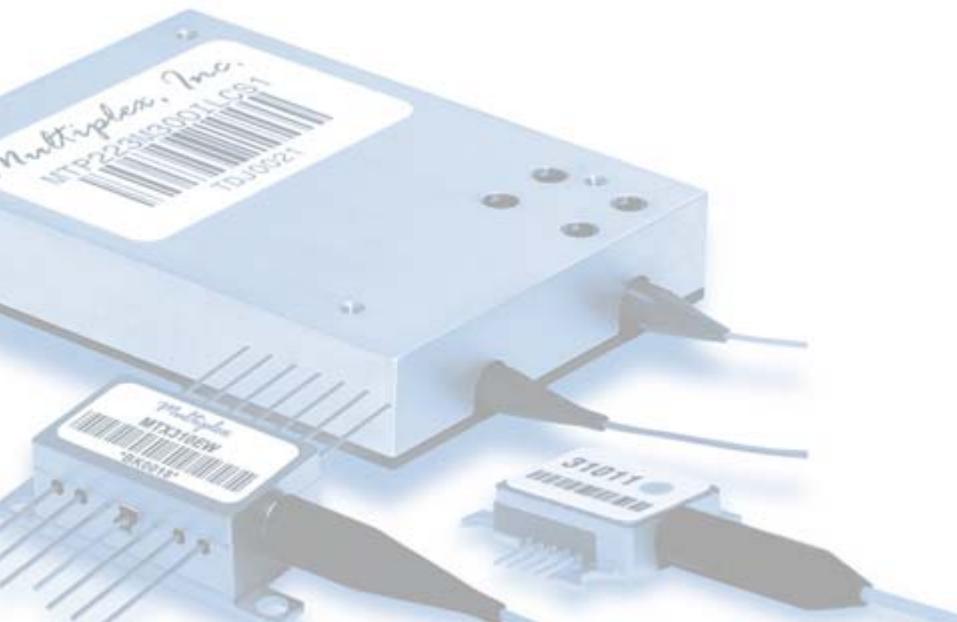


Photonics for Communications

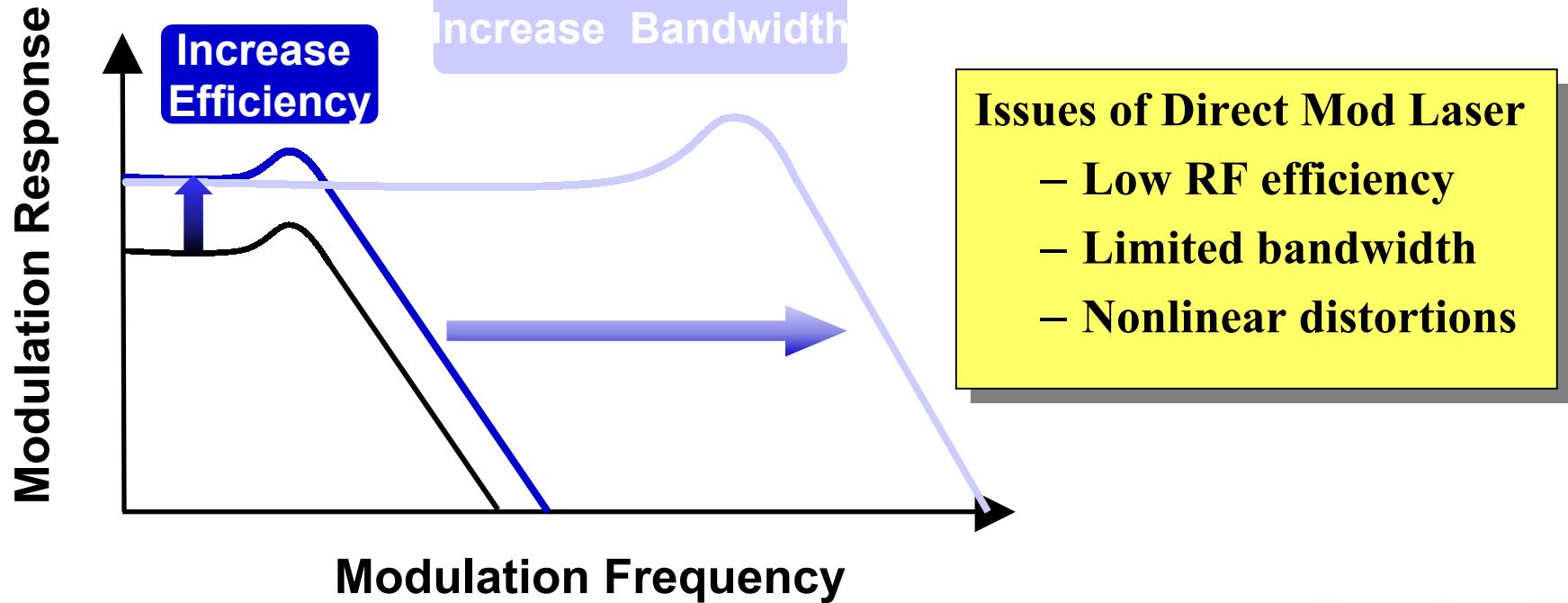
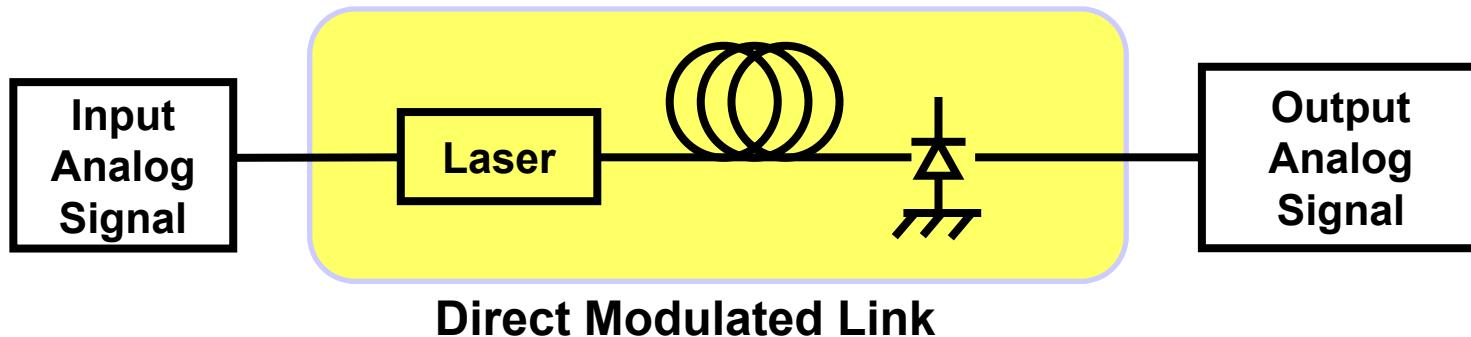
Introducing: Injection Locked Laser Transmitter

R&D Team: Multiplex Inc, UC Berkeley, UCSD

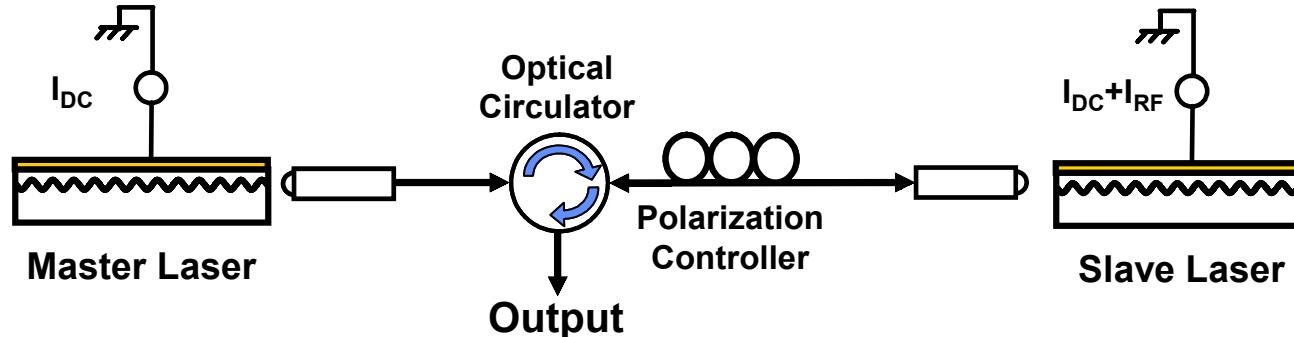
Sponsored by: DARPA RFLICS



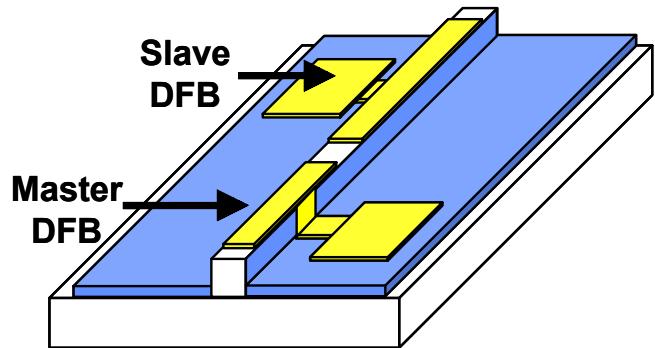
Directly Modulated Analog Fiber Optic Links



Monolithic Injection Locking Using Two Section DFB Laser



Conventional Optical Injection Locking: Bench Top



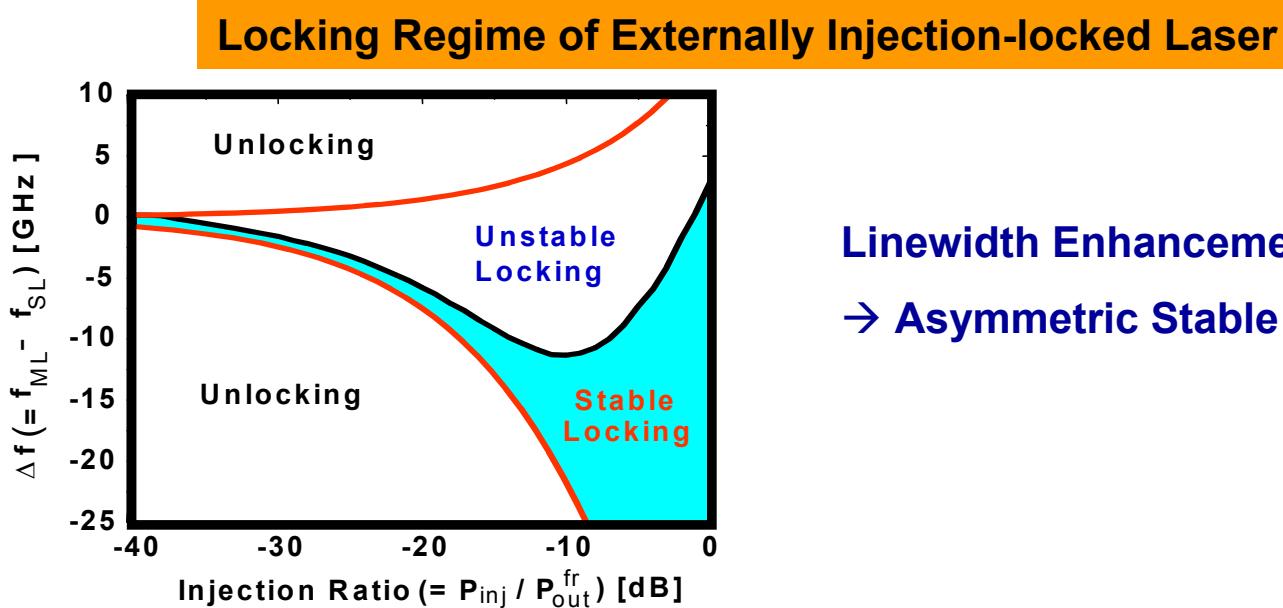
- Single laser package
- No optical isolator / circulator
- Automatic polarization match and optical alignment
- Current tuning
- Environmentally robust

New Monolithic Optical Injection Scheme Invented in RFLICS Program

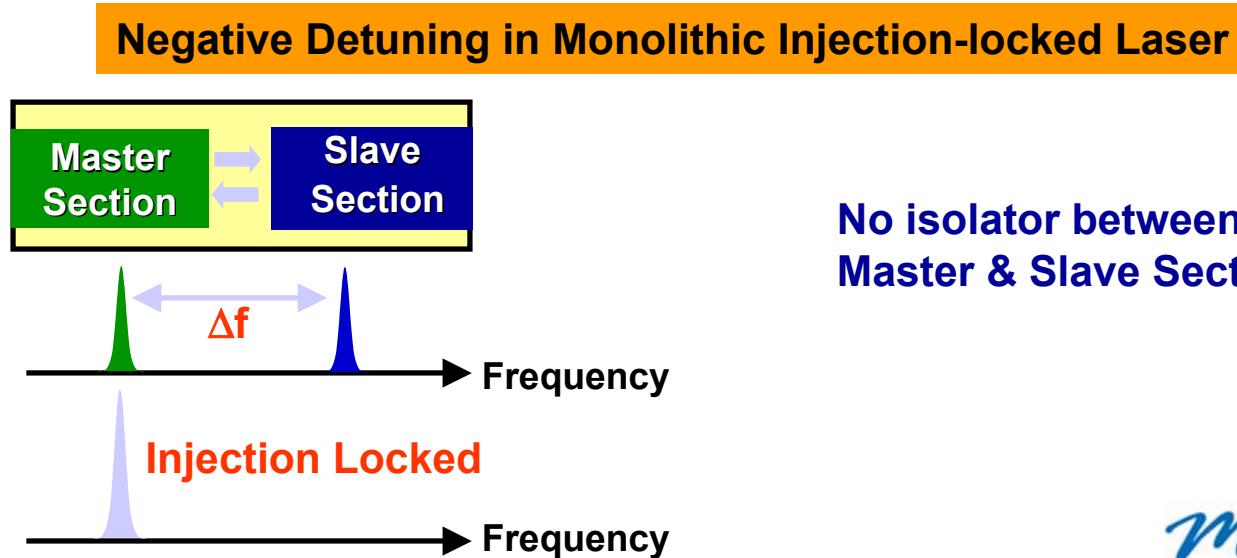
Multiplex
Photonics for Communications



Injection-locking by Two-section DFB Laser



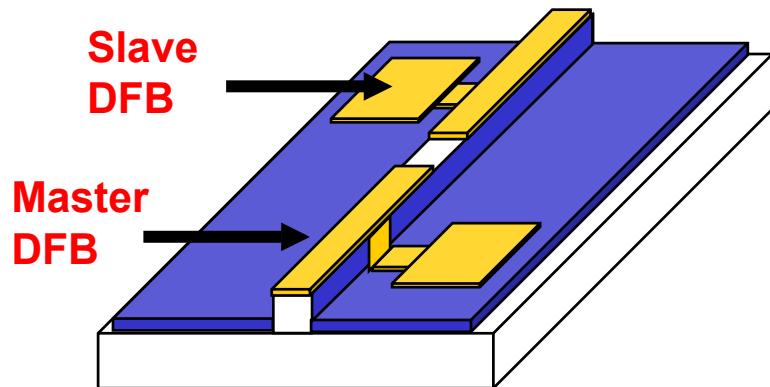
Linewidth Enhancement Factor α
→ Asymmetric Stable Locking Range



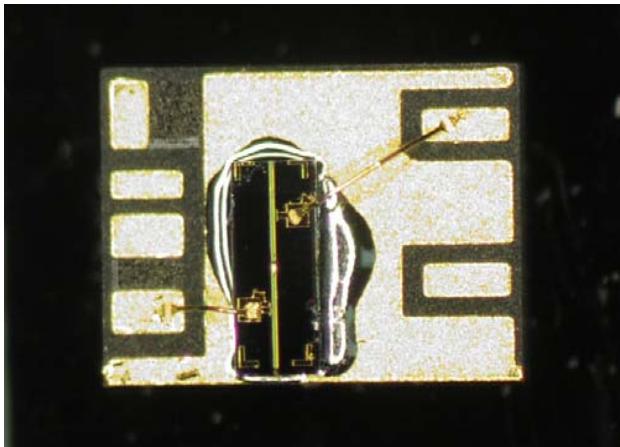
No isolator between
Master & Slave Section

Monolithic Injection Locking Using Two Section DFB Laser

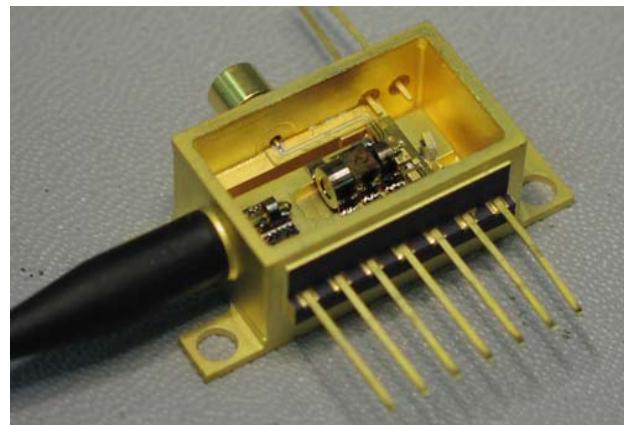
New Monolithic Optical Injection Scheme Invented in RFLICS Program



- Single laser package
- No optical isolator / circulator
- Automatic polarization match and optical alignment
- Current tuning
- Environmentally robust



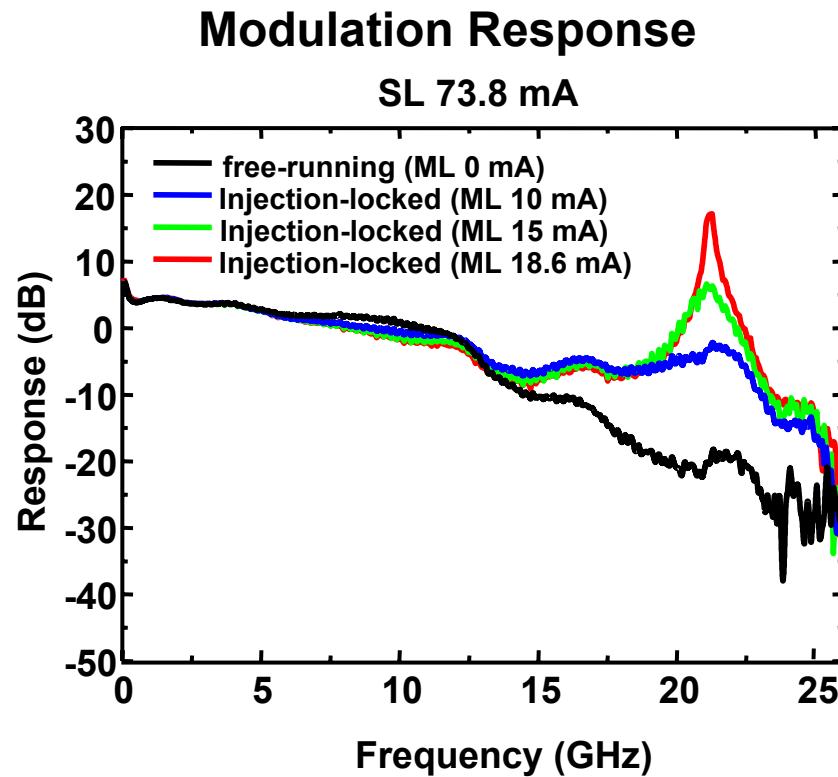
Integrated master-slave laser on submount with 25Ω termination for direct modulation



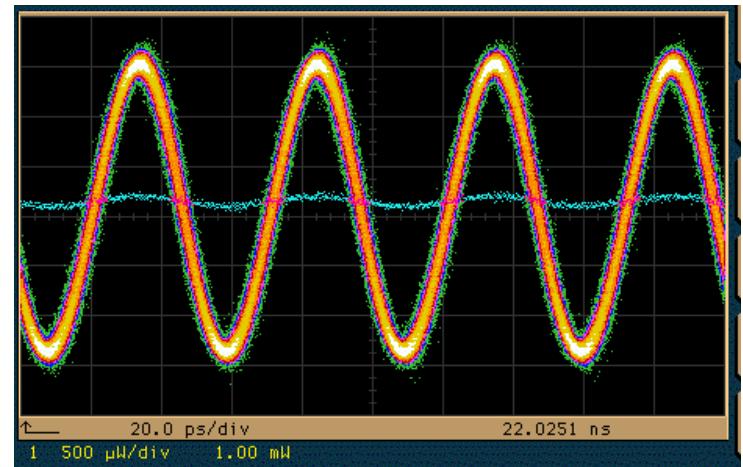
Fully packaged module with output fiber, optical isolator, master laser power monitor, TEC, RF input port



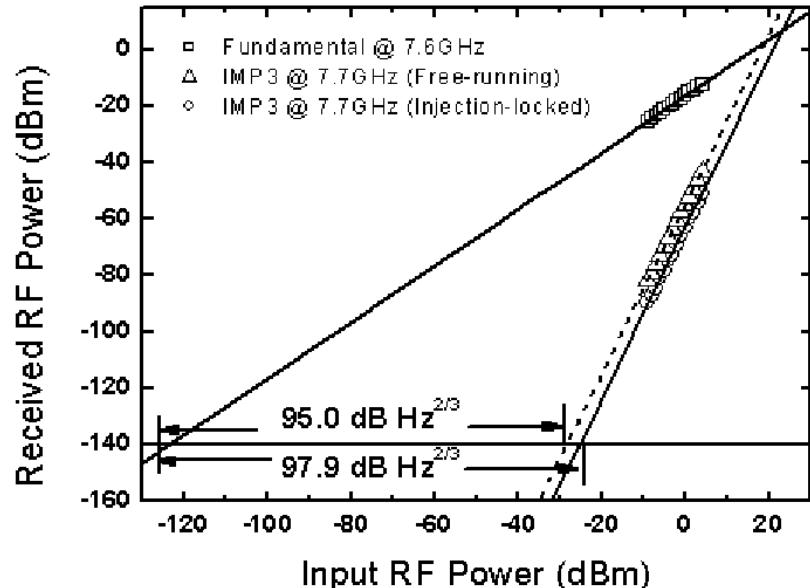
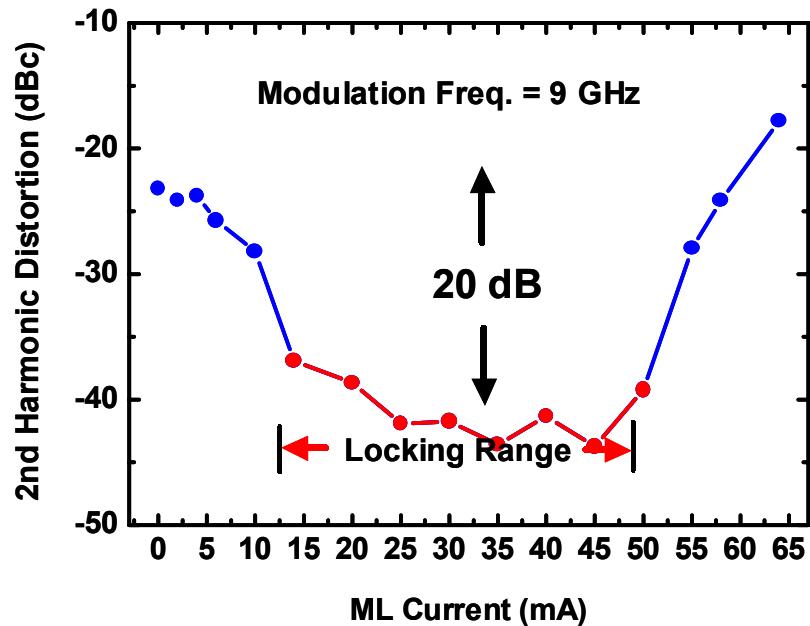
Monolithic Injection-locked laser in 25-GHz fiber-packaged module



**20 GHz Modulation
Applied to Slave Laser**



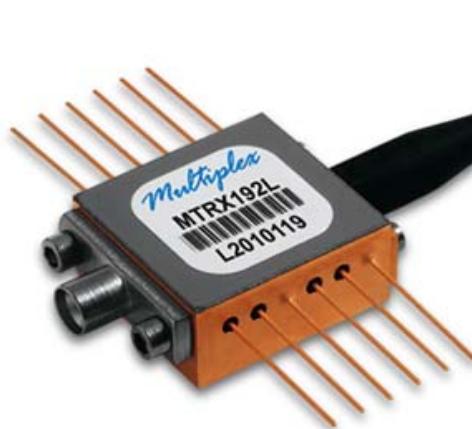
Monolithic Injection Locked DFB Laser



- Improved RF modulation linearity
- Suppression of harmonic distortion
- Increased spurious-free dynamic range
- Enhanced modulation bandwidth

Enhanced performance without increasing cost
by InP-InGaAsP chip integration

The Multiplex Family of Receivers



Gen-1 Receiver

PIN

Single Output

First with integrated
limiting amplifier

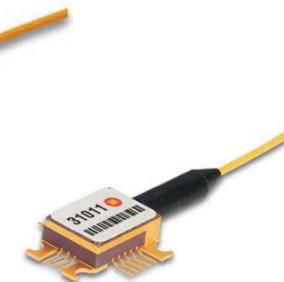


Gen-2 Receiver

PIN and APD versions

Co-planar differential
outputs

Small-form package



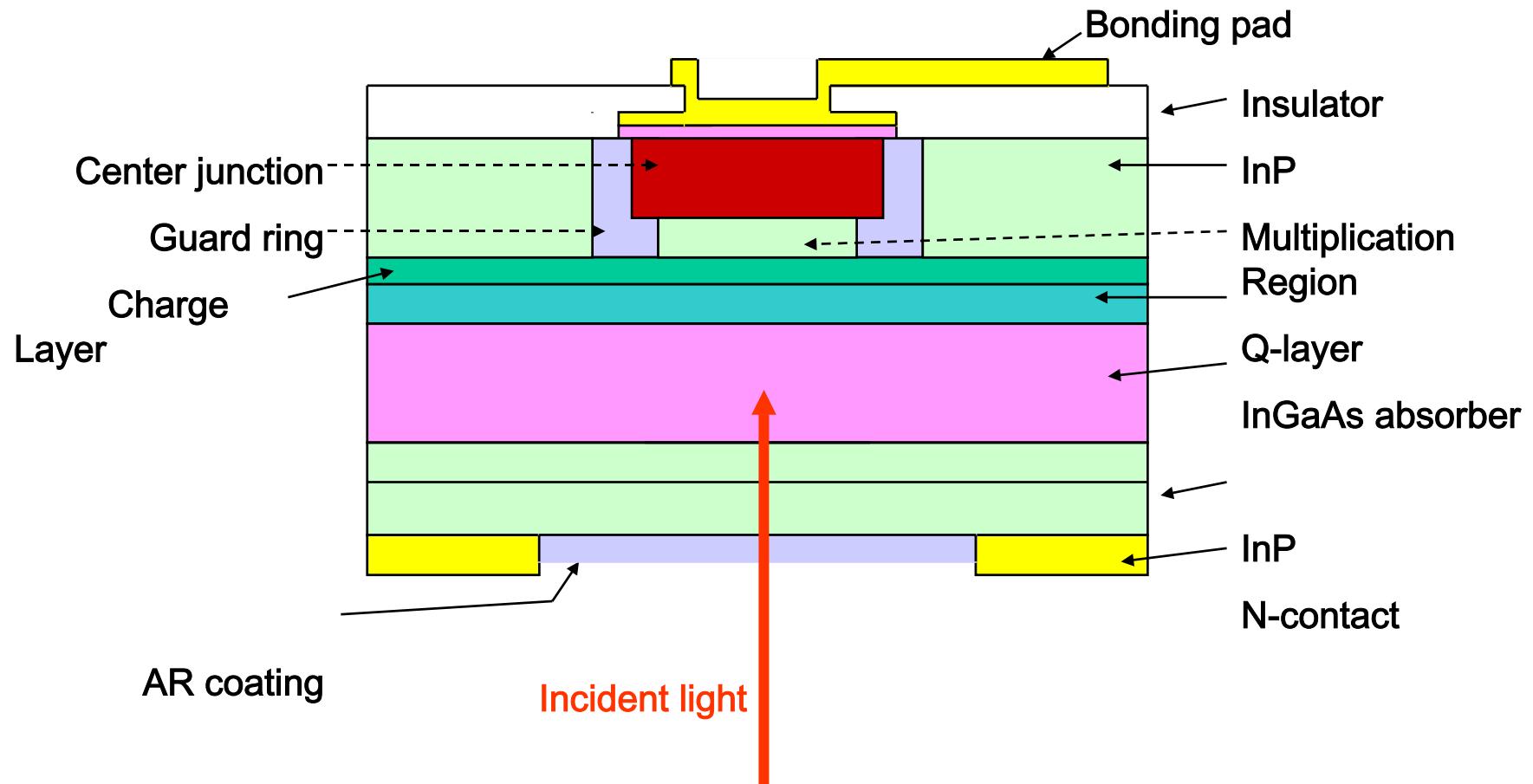
Gen-3 Receiver

PIN and APD versions

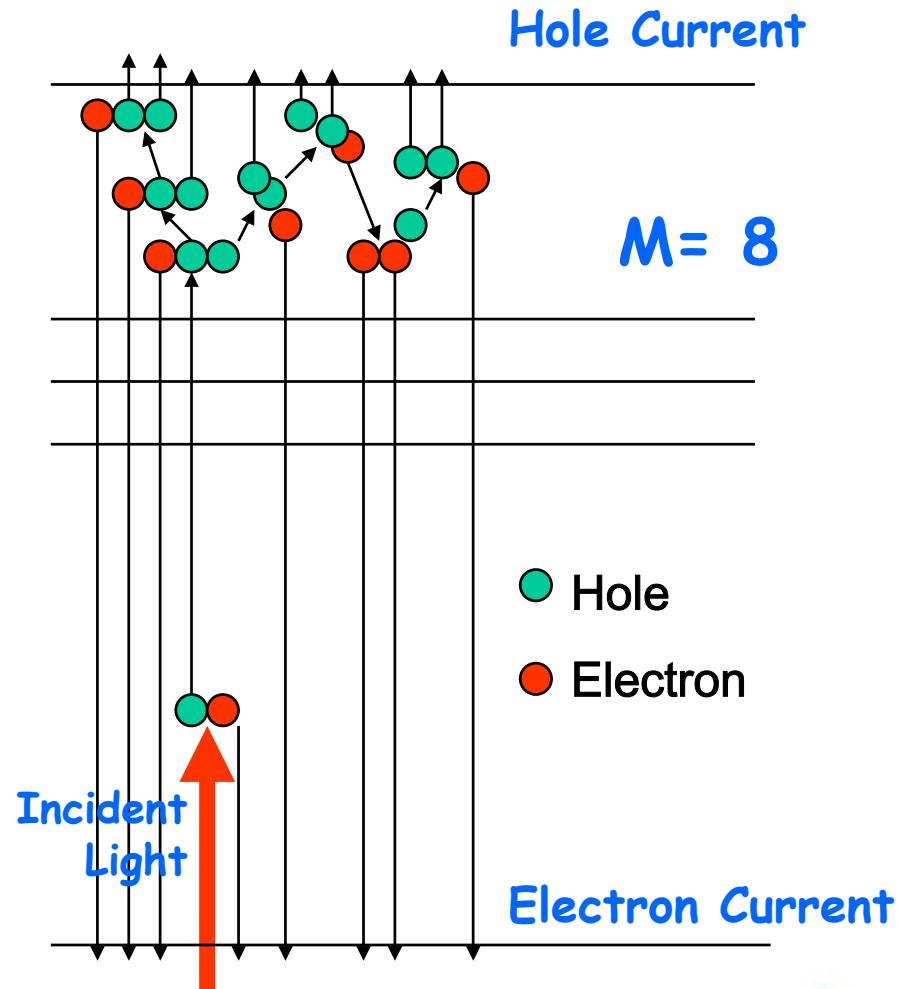
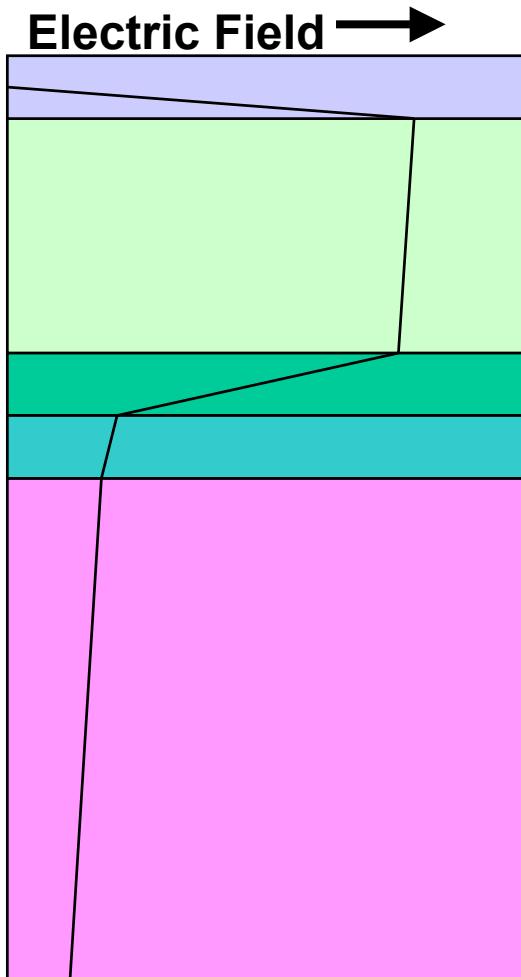
Ultra-compact surface-
mount MSA package

Unique “Gull-Wing” Pins
(> 20GHz BW)

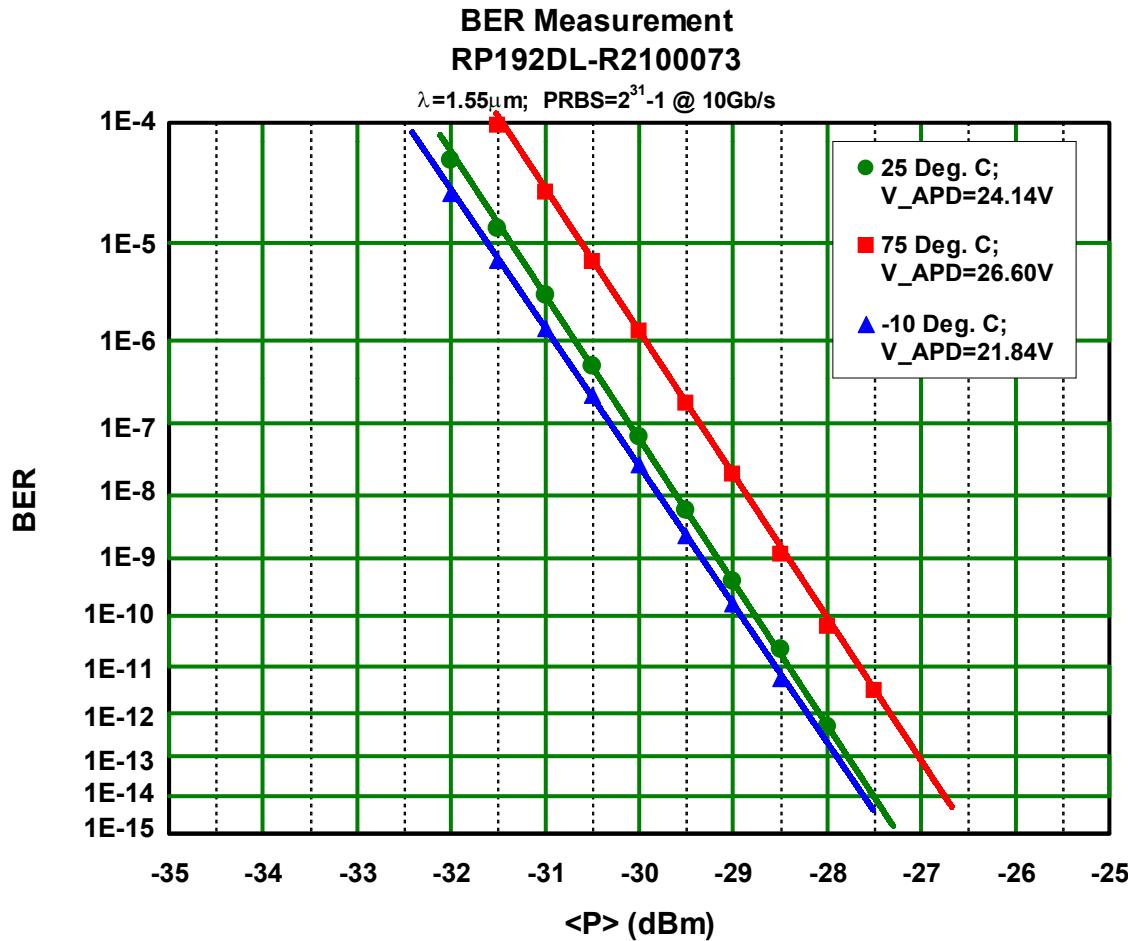
APD (Avalanche Photodiode) Design



Avalanche Multiplication



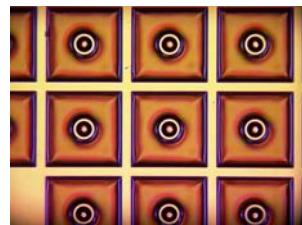
APD BER Measurement



Next Generation 10Gb Receiver Products

- **Ultra High Sensitivity APD Receiver:** 2-3 dB better sensitivity than the current APD receiver.

Sample: Q3/2005; Production Q4/2005



(Ultra Low Noise Lens APD)



- Dispersion Compensation Receivers: Optical dispersion compensation + Ultra High Sensitivity APD Receiver

Demonstration: Q2/2006



The Multiplex Family of Transponders



Gen-1 Transponder

200-pin MSA

**MSA small-form-factor:
2" x 3" x 0.5"**

1310 or 1550nm EML



Gen-2 Transponder

300-pin MSA

**MSA small-form-factor:
2.2" x 3" x 0.56"**

PIN and APD versions



Gen-3 Transponder

300-pin MSA Flat-Top

Ability to mount customer-designed external heat sink

DWDM ITU wavelength locked (stabilized)

Tunable over 16 channels

PIN and APD versions

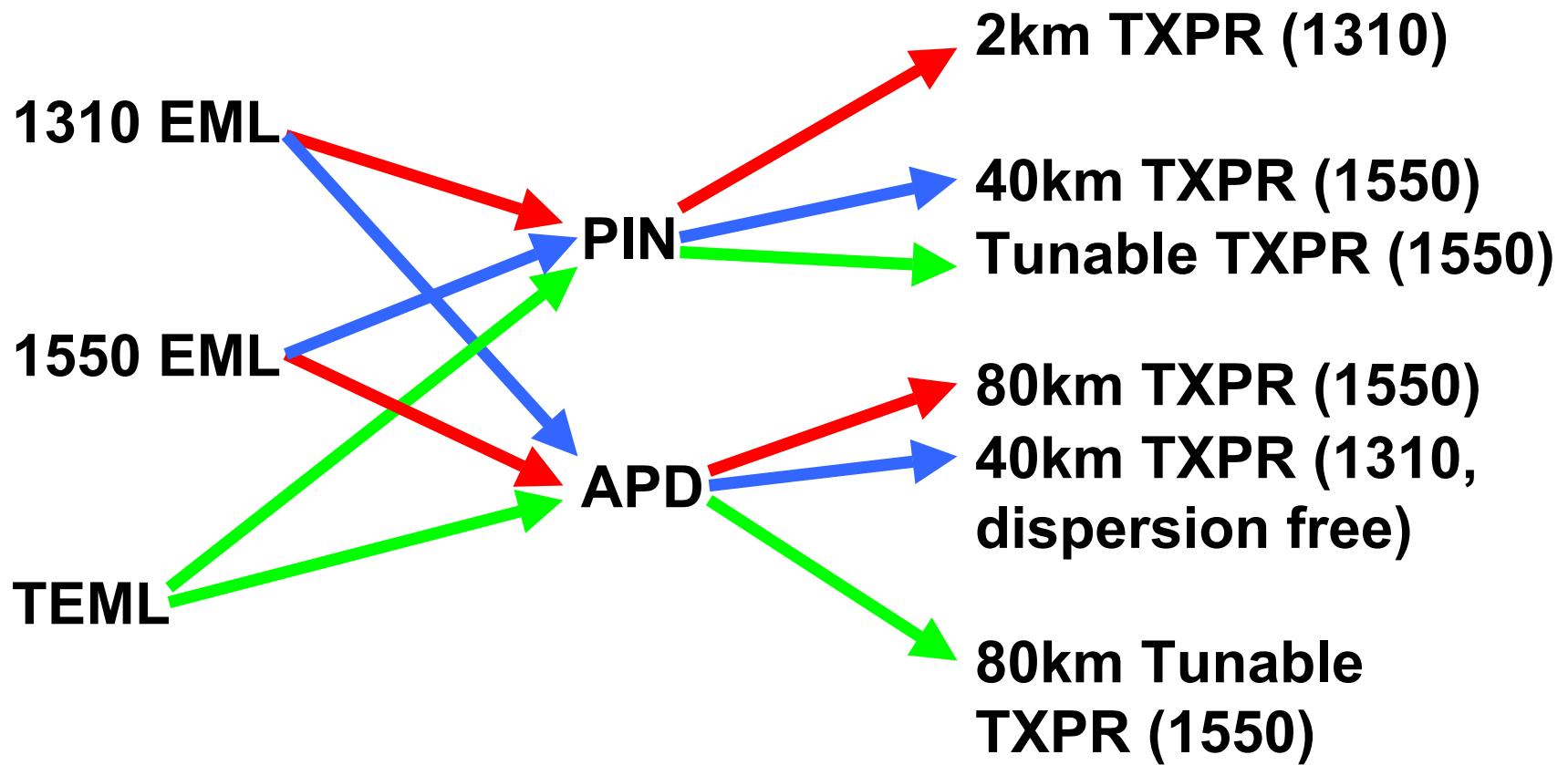
**SR-1, SR-2, IR-1, IR-2
and LR-2**

Multiplex



Photonics for Communications

The Power of Vertical Integration



Core Technology Building Blocks

Technology:

Custom-Design Systems

Subsystems

Modules

Chips

MOCVD growth & Processing

Vertical Integration

Expertise:

INTEGRATION

Packaging and Assembly

RF Design

Optical Design

IC Design

APD

PIN

EML

TEML

PUMP

EPI-Wafer Growth & Chip Processing

Expanding

Products:

Custom Systems
Transponders
Tunable EMLs
Pump Combiner

EMLs
Receivers
Pump

Chips

Foundry Services



Multiplex Facilities



Corporate Headquarters
& Front-End Manufacturing
- MOCVD wafer growth
- Chip fabrication
- Administration

Back-End Manufacturing

- Module packaging
- Subsystem Assembly

High-Speed Design Center



Facilities are located in South Plainfield, New Jersey

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